354 9 7-15-02 PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Shin-itsu TAKEHASHI et al.

Serial No.: New Application

Group Art Unit:

Filed: March 18, 2002

Examiner:

For: THIN FILM TRANSISTOR AND METHOD FOR FABRICATING THE SAME

PRELIMINARY AMENDMENT

Commissioner for Patents Washington, D.C. 20231

Sir:

Prior to examination of the above-identified application, please enter the following changes:

IN THE CLAIMS:

Please cancel claims 20 to 23, 27, 30, 31, 40, and 47 to 51 without prejudice or disclaimer.

Please amend the claims as follows:

16. (Amended) The method for fabricating an LDD thin film transistor in accordance with claim 1, wherein in the isolated